

PATENT ASSIGNMENT

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SUBMISSION TYPE:	NEW ASSIGNMENT										
NATURE OF CONVEYANCE:	ASSIGNMENT										
CONVEYING PARTY DATA											
<table border="1"> <thead> <tr> <th>Name</th> <th>Execution Date</th> </tr> </thead> <tbody> <tr> <td>NAOTO UMEZAWA</td> <td>09/20/2013</td> </tr> <tr> <td>TOYOHIRO CHIKYO</td> <td>09/21/2013</td> </tr> <tr> <td>TOSHIHIDE NABATAME</td> <td>09/27/2013</td> </tr> </tbody> </table>		Name	Execution Date	NAOTO UMEZAWA	09/20/2013	TOYOHIRO CHIKYO	09/21/2013	TOSHIHIDE NABATAME	09/27/2013		
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<table border="1"> <tr> <td>Name:</td> <td>NATIONAL INSTITUTE FOR MATERIALS SCIENCE</td> </tr> <tr> <td>Street Address:</td> <td>2-1, SENGEN 1-CHOME, TSUKUBA-SHI</td> </tr> <tr> <td>City:</td> <td>IBARAKI</td> </tr> <tr> <td>State/Country:</td> <td>JAPAN</td> </tr> <tr> <td>Postal Code:</td> <td>305-0047</td> </tr> </table>		Name:	NATIONAL INSTITUTE FOR MATERIALS SCIENCE	Street Address:	2-1, SENGEN 1-CHOME, TSUKUBA-SHI	City:	IBARAKI	State/Country:	JAPAN	Postal Code:	305-0047
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PROPERTY NUMBERS Total: 1											
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CORRESPONDENCE DATA											
<p>Fax Number: (203)575-2600 <i>Correspondence will be sent via US Mail when the fax attempt is unsuccessful.</i></p> <p>Phone: (203) 578-4229 Email: lfreed@carmodylaw.com Correspondent Name: JOHN L. CORDANI Address Line 1: 50 LEAVENWORTH STREET Address Line 2: P.O. BOX 1110 Address Line 4: WATERBURY, CONNECTICUT 06721-1110</p>											
ATTORNEY DOCKET NUMBER:	27231-26B										
NAME OF SUBMITTER:	LINDA M. FREED										
Signature:	/Linda M. Freed/										

Date:

10/04/2013

Total Attachments: 3

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ASSIGNMENT

WHEREAS, we,

NAOTO UMEZAWA, c/o National Institute for Materials Science, 2-1, Sengen 1-chome, Tsukuba-shi, Ibaraki 305-0047 Japan; **TOYOHIRO CHIKYO**, c/o National Institute for Materials Science, 2-1, Sengen 1-chome, Tsukuba-shi, Ibaraki 305-0047 Japan; and **TOSHIHIDE NABATAME**, c/o National Institute for Materials Science, 2-1, Sengen 1-chome, Tsukuba-shi, Ibaraki 305-0047 Japan; having made an invention entitled **Method for Reducing Thickness of Interfacial Layer, Method for Forming High Dielectric Constant Gate Insulating Film, High Dielectric Constant Gate Insulating Film, High Dielectric Constant Gate Oxide Film, and Transistor Having High Dielectric Constant Gate Oxide Film**, Attorney Docket No. 27231-26B, an application for which a Patent of the United States of America is being executed concurrently herewith; or

We hereby authorize and request John L. Cordani, of Carmody & Torrance LLP, 50 Leavenworth Street, P.O. Box 1110, Waterbury, CT 06721-1110 to insert the filing date and application number of said application when known in the spaces provided below:

Filing Date:	<u>October 4, 2013</u>
U.S. Serial Application No.:	<u>14/046,339</u>

NOW, THEREFORE, for good and valuable consideration, receipt of which is acknowledged, we have agreed to assign and transfer and do hereby assign and transfer unto **National Institute for Materials Science**, having an office and place of business at 2-1, Sengen 1-chome, Tsukuba-shi, Ibaraki 305-0047 Japan, its successors and assigns, the entire right, title and interest in and to the said invention and application, and in and to any divisional, continuation or continuation-in-part, of said application, and in and to any and all patents and reissues and extensions thereof, of the United States of America,

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which have been or may be granted on any of the foregoing to be held and enjoyed as fully and exclusively as they would have been by us had this assignment and transfer not been made;

We do further agree for ourselves and for our heirs, executors and administrators to execute and deliver without further consideration any further applications, assignments and documents, and to perform such other acts as we lawfully may, that may be deemed necessary by the said **National Institute for Materials Science**, its successors, assigns, and nominees, fully to secure their interest as aforesaid and to obtain or maintain patents in the United States of America;

And we do hereby authorize and request the Commissioner of Patents to issue any and all patents which may be granted upon any of the said applications, to the said **National Institute for Materials Science**, as the assignee of the entire interest therein.

IN TESTIMONY WHEREOF, we have hereunto signed our names on the date indicated hereinafter.

Naoto Umezawa
NAOTO UMEZAWA

September 20, 2013
Date

SIGNED IN THE PRESENCE OF WITNESSES:

(1) _____
Print Name:

Date: _____

(2) _____
Print Name:

Date: _____

{W2295899}

Toyohiro Chikyo
TOYOHIRO CHIKYO

21/09/2013
Date

SIGNED IN THE PRESENCE OF WITNESSES:

(1) _____
Print Name:

(2) _____
Print Name:

Date: _____

Date: _____

Toshihide Nabatame
TOSHIHIDE NABATAME

24/09/2013
Date

SIGNED IN THE PRESENCE OF WITNESSES:

(1) _____
Print Name:

(2) _____
Print Name:

Date: _____

Date: _____

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